MOSFET -3.5 Amps, -30 Volts

P-Channel TSOP-6

Features

- Ultra Low R_{DS(on)}
- Higher Efficiency Extending Battery Life
- Miniature TSOP-6 Surface Mount Package
- Pb-Free Package is Available

Applications

 Power Management in Portable and Battery-Powered Products, i.e.: Cellular and Cordless Telephones, and PCMCIA Cards

MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise noted.)

,			
Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	-30	Volts
Gate-to-Source Voltage - Continuous	V_{GS}	±20.0	Volts
Thermal Resistance Junction-to-Ambient (Note 1.) Total Power Dissipation @ T _A = 25°C Drain Current - Continuous @ T _A = 25°C - Pulsed Drain Current (T _p < 10 μS) Maximum Operating Power Dissipation Maximum Operating Drain Current	R _{θJA} P _d I _D I _{DM} P _d I _D	62.5 2.0 -3.5 -20 1.0 -2.5	°C/W Watts Amps Amps Watts Amps
Thermal Resistance Junction-to-Ambient (Note 2.) Total Power Dissipation @ T _A = 25°C Drain Current - Continuous @ T _A = 25°C - Pulsed Drain Current (T _p < 10 μS) Maximum Operating Power Dissipation Maximum Operating Drain Current	R ₀ JA Pd I _D I _{DM} Pd I _D	128 1.0 -2.5 -14 0.5 -1.75	°C/W Watts Amps Amps Watts Amps
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to 150	°C
Maximum Lead Temperature for Soldering Purposes for 10 Seconds	TL	260	°C

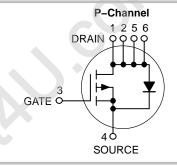
- 1. Mounted onto a 2" square FR-4 board (1" sq. 2 oz. cu. 0.06" thick single sided), t < 5.0 seconds.
- Mounted onto a 2" square FR-4 board (1" sq. 2 oz. cu. 0.06" thick single sided), operating to steady state.



ON Semiconductor®

http://onsemi.com

V _{(BR)DSS}	R _{DS(on)} TYP	I _D Max
-30 V	100 mΩ @ –10 V	−3.5 A



MARKING DIAGRAM

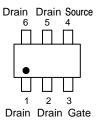


TSOP-6 CASE 318G STYLE 1



455 = Device Code x = Date Code

PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping [†]
NTGS3455T1	TSOP-6	3000 Tape & Reel
NTGS3455T1G	TSOP-6 (Pb-Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Notes 3. & 4.)

Cha	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Drain–Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = –10 μA)		V _{(BR)DSS}	-30	_	-	Vdc
Zero Gate Voltage Drain Current $ (V_{GS} = 0 \text{ Vdc}, V_{DS} = -30 \text{ Vdc}, T_J = 25^{\circ}\text{C}) $ $ (V_{GS} = 0 \text{ Vdc}, V_{DS} = -30 \text{ Vdc}, T_J = 70^{\circ}\text{C}) $		I _{DSS}	- -	- -	-1.0 -5.0	μAdc
Gate-Body Leakage Current (V _{GS} = -20.0 Vdc, V _{DS} = 0 Vdc)		I _{GSS}	_	_	-100	nAdc
Gate-Body Leakage Current (V _{GS} = +20.0 Vdc, V _{DS} = 0 Vdc	I _{GSS}	-	_	100	nAdc	
ON CHARACTERISTICS						
Gate Threshold Voltage $(V_{DS} = V_{GS}, I_D = -250 \mu Adc)$		V _{GS(th)}	-1.0	-1.87	-3.0	Vdc
Static Drain–Source On–State Resistance $(V_{GS} = -10 \text{ Vdc}, I_D = -3.5 \text{ Adc})$ $(V_{GS} = -4.5 \text{ Vdc}, I_D = -2.7 \text{ Adc})$		R _{DS(on)}	_ _	0.094 0.144	0.100 0.170	Ω
Forward Transconductance ($V_{DS} = -15 \text{ Vdc}$, $I_D = -3.5 \text{ Adc}$)		9FS	_	6.0	_	mhos
DYNAMIC CHARACTERISTICS						
Total Gate Charge	<i></i>	Q _{tot}	_	9.0	13	nC
Gate-Source Charge	$(V_{DS} = -15 \text{ Vdc}, V_{GS} = -10 \text{ Vdc}, I_{D} = -3.5 \text{ Adc})$	Q_{gs}	_	2.5	_	
Gate-Drain Charge	,	Q_{gd}	_	2.0	_	
Input Capacitance	0/ 50/ds // 0/ds	C _{iss}	1	480	_	pF
Output Capacitance	$(V_{DS} = -5.0 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, $ f = 1.0 MHz)	C _{oss}	_	220	_	
Reverse Transfer Capacitance	,	C _{rss}	_	60	_	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time		t _{d(on)}	_	10	20	ns
Rise Time	$(V_{DD} = -20 \text{ Vdc}, I_D = -1.0 \text{ Adc},$	t _r	_	15	30	
Turn-Off Delay Time	$V_{GS} = -10 \text{ Vdc}, R_g = 6.0 \Omega$	t _{d(off)}	1	20	35	
Fall Time		t _f	_	10	20	
Reverse Recovery Time	$(I_S = -1.7 \text{ Adc}, dI_S/dt = 100 \text{ A/}\mu\text{s})$	t _{rr}	_	30	-	ns
BODY-DRAIN DIODE RATINGS						
Diode Forward On-Voltage	$(I_S = -1.7 \text{ Adc}, V_{GS} = 0 \text{ Vdc})$	V _{SD}	_	-0.90	-1.2	Vdc
Diode Forward On-Voltage	$(I_S = -3.5 \text{ Adc}, V_{GS} = 0 \text{ Vdc})$	V _{SD}	_	-1.0	_	Vdc
·	·					

Indicates Pulse Test: P.W. = 300 μsec max, Duty Cycle = 2%.
 Class 1 ESD rated – Handling precautions to protect against electrostatic discharge is mandatory.

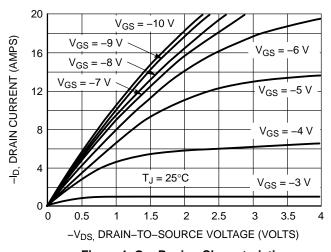


Figure 1. On-Region Characteristics

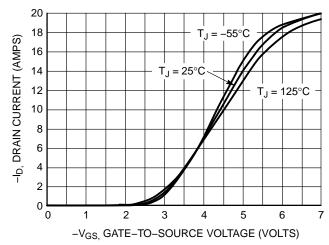


Figure 2. Transfer Characteristics

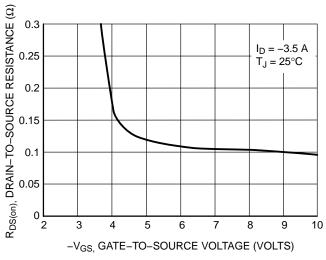


Figure 3. On-Resistance vs. Gate-to-Source Voltage

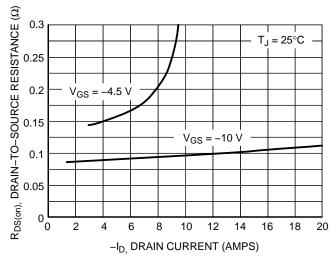


Figure 4. On-Resistance vs. Drain Current and **Gate Voltage**

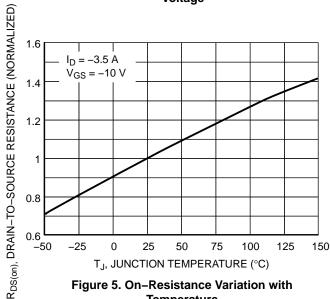


Figure 5. On-Resistance Variation with **Temperature**

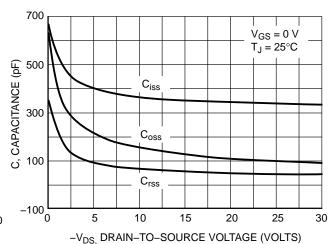
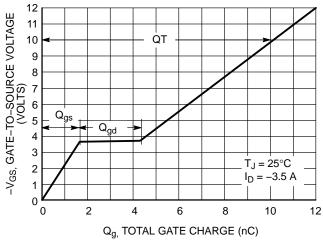


Figure 6. Capacitance Variation



10 V_{GS} = 0 V V_{GS} = 0 V T_J = 150°C T_J = 25°C T_J = 25°C V_{SD}, SOURCE-TO-DRAIN VOLTAGE (VOLTS)

Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

Figure 8. Diode Forward Voltage vs. Current

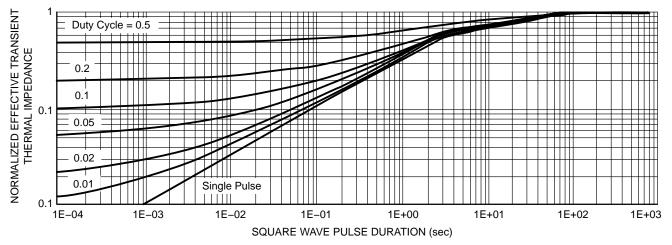


Figure 9. Normalized Thermal Transient Impedance, Junction-to-Ambient

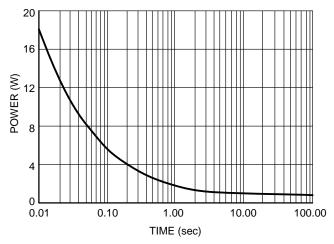
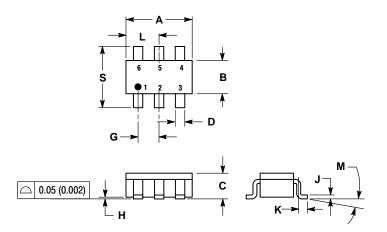


Figure 10. Single Pulse Power

PACKAGE DIMENSIONS

TSOP-6 CASE 318G-02 ISSUE G



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.1142	0.1220
В	1.30	1.70	0.0512	0.0669
С	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.05	0.0335	0.0413
Н	0.013	0.100	0.0005	0.0040
J	0.10	0.26	0.0040	0.0102
K	0.20	0.60	0.0079	0.0236
L	1.25	1.55	0.0493	0.0610
M	0 °	10°	0 °	10°
S	2.50	3.00	0.0985	0.1181

- STYLE 1:
 PIN 1. DRAIN
 2. DRAIN
 3. GATE
 4. SOURCE
 5. DRAIN
 6. DRAIN

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